# ne<mark>x</mark>peria

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Kind regards,

Team Nexperia

NPN/PNP resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = open

Rev. 02 — 2 September 2009

**Product data sheet** 

### 1. Product profile

#### 1.1 General description

NPN/PNP resistor-equipped transistors

Table 1.	Product	overview
	1 I O G G G C	010111011

Type number	Package	Package		NPN/NPN complement	
	NXP	JEITA			
PEMD14	SOT666	-	PEMB14	PEMH14	
PUMD14	SOT363	SC-88	PUMB14	PUMH14	

#### 1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place cost

#### **1.3 Applications**

- Low current peripheral driver
- Control of IC inputs
- Replacement of general-purpose transistors in digital applications

#### 1.4 Quick reference data

Quick reference data					
Parameter	Conditions	Min	Тур	Max	Unit
collector-emitter voltage	open base	-	-	50	V
output current (DC)		-	-	100	mA
bias resistor 1 (input)		33	47	61	kΩ
	Parameter collector-emitter voltage output current (DC)	ParameterConditionscollector-emitter voltageopen baseoutput current (DC)	ParameterConditionsMincollector-emitter voltageopen base-output current (DC)-	ParameterConditionsMinTypcollector-emitter voltageopen baseoutput current (DC)	ParameterConditionsMinTypMaxcollector-emitter voltageopen base50output current (DC)100



*006aaa269* 

#### NPN/PNP resistor-equipped transistors; R1 = 47 kΩ, R2 = open

# 2. Pinning information

Table 3.	Pinning		
Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1	001aab555	R1
			1 2 3

# 3. Ordering information

Table 4.	Ordering	information
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Type number	Package		
	Name	Description	Version
PEMD14	-	plastic surface mounted package; 6 leads	SOT666
PUMD14	SC-88	plastic surface mounted package; 6 leads	SOT363

### 4. Marking

Table 5. Marking codes	
Type number	Marking code <sup>[1]</sup>
PEMD14	5B
PUMD14	T2*

[1] \* = -: made in Hong Kong

\* = p: made in Hong Kong

\* = t: made in Malaysia

\* = W: made in China

#### NPN/PNP resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = open

### 5. Limiting values

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor; for the PNP transistor v	with negative polar	ity		
V <sub>CBO</sub>	collector-base voltage	open emitter	-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	5	V
lo	output current (DC)		-	100	mA
I <sub>CM</sub>	peak collector current		-	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363		<u>[1]</u> _	200	mW
	SOT666		<u>[1] [2]</u> _	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
Per device	)				
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363		<u>[1]</u> _	300	mW
	SOT666		[1] [2] _	300	mW

[1] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

### 6. Thermal characteristics

Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Per trans	istor					
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$				
	SOT363		<u>[1]</u> -	-	625	K/W
	SOT666		<u>[1] [2]</u> _	-	625	K/W
Per devic	e					
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$				
	SOT363		<u>[1]</u> -	-	416	K/W
	SOT666		<u>[1]</u> <u>[2]</u> _	-	416	K/W

[1] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

NPN/PNP resistor-equipped transistors; R1 = 47 kΩ, R2 = open

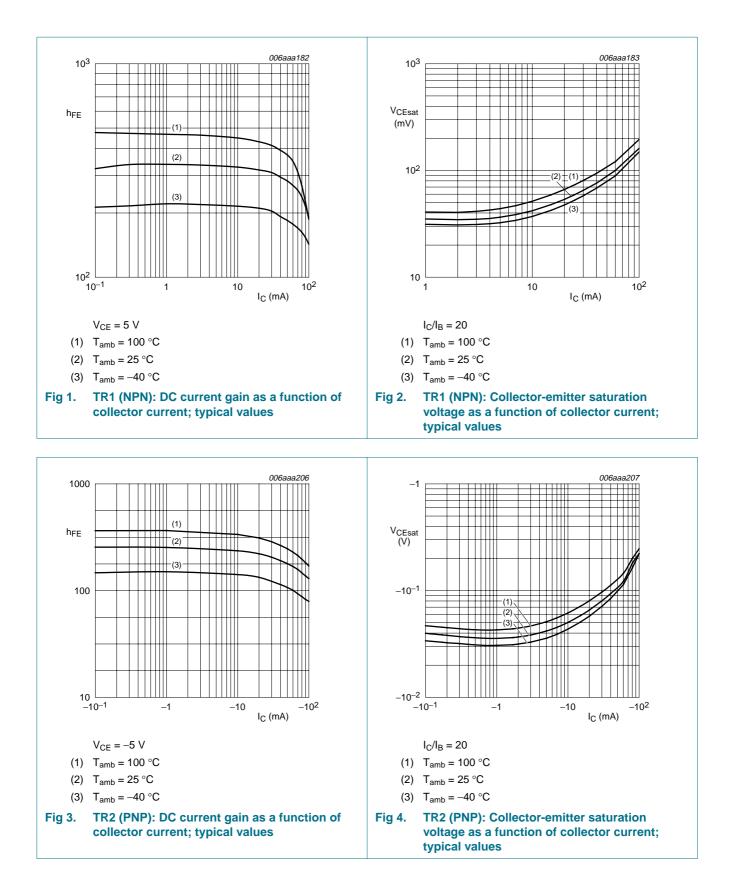
# 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Per transis	stor; for the PNP transis	tor with negative polarity				
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I <sub>CEO</sub>	collector-emitter	$V_{CE} = 30 \text{ V}; \text{ I}_{B} = 0 \text{ A}$	-	-	1	μA
	cut-off current	$V_{CE} = 30 \text{ V}; I_B = 0 \text{ A};$ T <sub>j</sub> = 150 °C	-	-	50	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; \text{ I}_{C} = 1 \text{ mA}$	100	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C}$ = 10 mA; $I_{B}$ = 0.5 mA	-	-	150	mV
R1	bias resistor 1 (input)		33	47	61	kΩ
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; \text{ I}_{E} = \text{i}_{e} = 0 \text{ A};$ f = 1 MHz				
	TR1 (NPN)		-	-	2.5	pF
	TR2 (PNP)		-	-	3	pF

#### **NXP Semiconductors**

# PEMD14; PUMD14

#### NPN/PNP resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = open

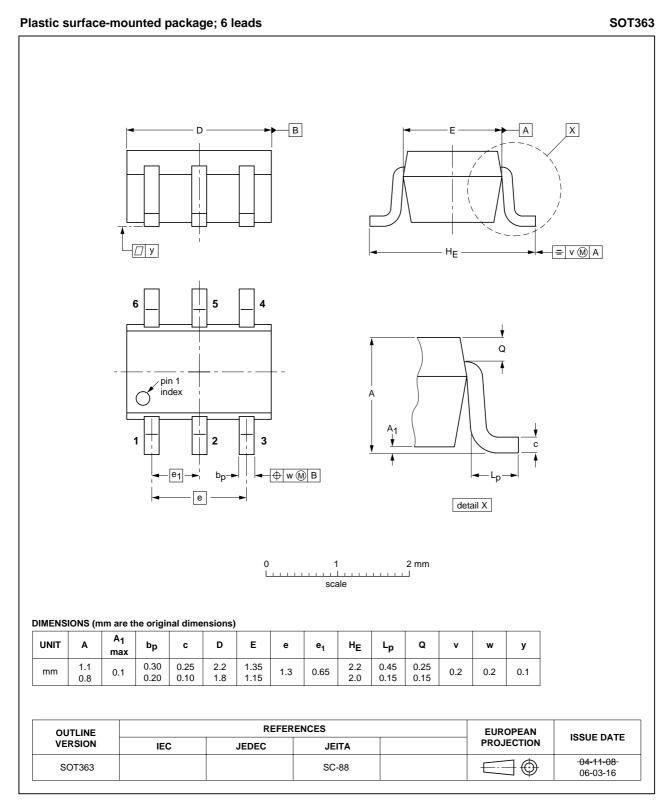


#### **NXP Semiconductors**

PEMD14; PUMD14

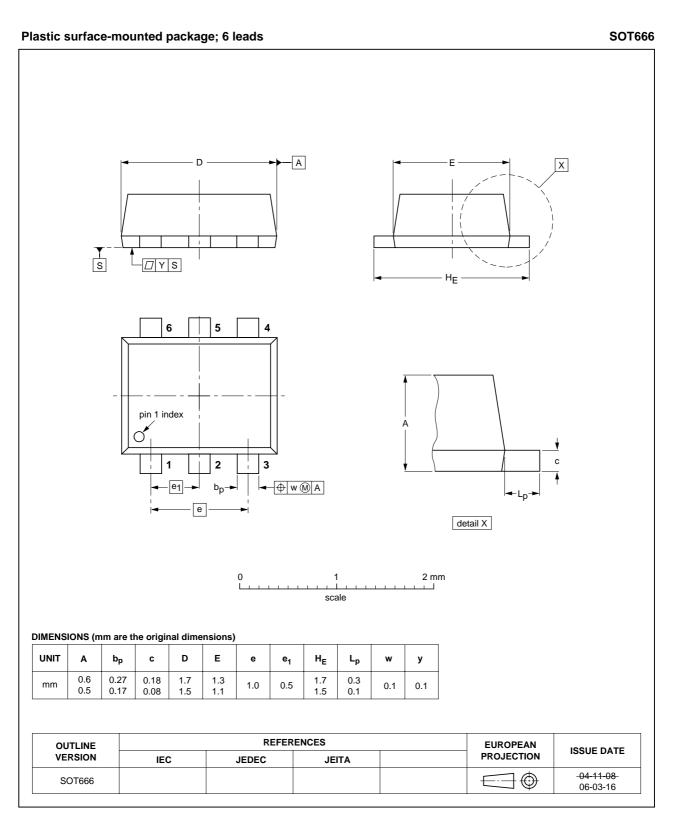
NPN/PNP resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = open

### 8. Package outline



#### Fig 5. Package outline SOT363 (SC-88)

NPN/PNP resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = open



#### Fig 6. Package outline SOT666

PEMD14\_PUMD14\_2

NPN/PNP resistor-equipped transistors; R1 = 47 kΩ, R2 = open

# 9. Packing information

#### Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description	Packing of	quantity	
			3000	4000	10000
PEMD14	SOT666	4 mm pitch, 8 mm tape and reel	-	-115	-
PUMD14	SOT363	4 mm pitch, 8 mm tape and reel; T1	2 -115	-	-135
PUMD14	SOT363	4 mm pitch, 8 mm tape and reel; T2	<mark>3]</mark> -125	-	-165

[1] For further information and the availability of packing methods, see Section 12.

[2] T1: normal taping

[3] T2: reverse taping

NPN/PNP resistor-equipped transistors; R1 = 47 kΩ, R2 = open

# **10. Revision history**

Table 10. Revision hist	ory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMD14_PUMD14_2	20090902	Product data sheet	-	PEMD14_PUMD14_1
Modifications:		et was changed to reflect legal definitions and disc		e NXP Semiconductors, ere made to the technical
	<ul> <li>Figure 5 "Pack</li> </ul>	kage outline SOT363 (SC	-88)": updated	
	<ul> <li>Figure 6 "Pack</li> </ul>	kage outline SOT666": up	dated	
PEMD14_PUMD14_1	20050114	Product data sheet	-	-

# **11. Legal information**

#### 11.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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PEMD14\_PUMD14\_2
Product data sheet

#### **NXP Semiconductors**

# PEMD14; PUMD14

NPN/PNP resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = open

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